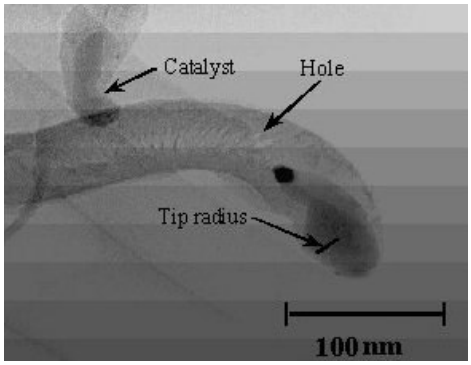
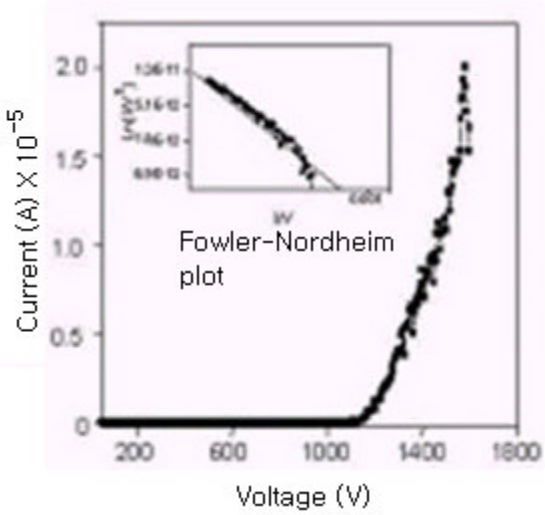
ATS-CVD Series
PECVD System for Low Temp. CNTs Synthesis

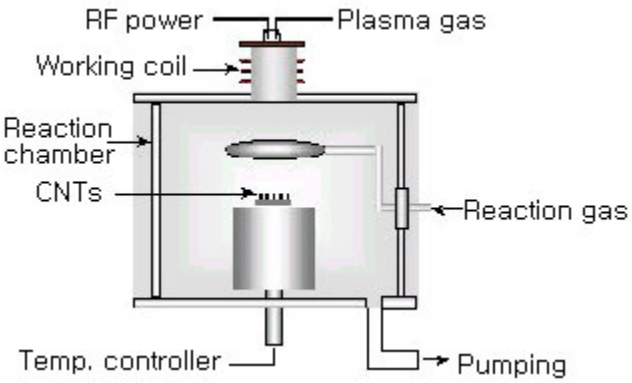
TEM images of CNTs using PECVD



I-V curve of CNTs using PECVD



Schematic Diagram



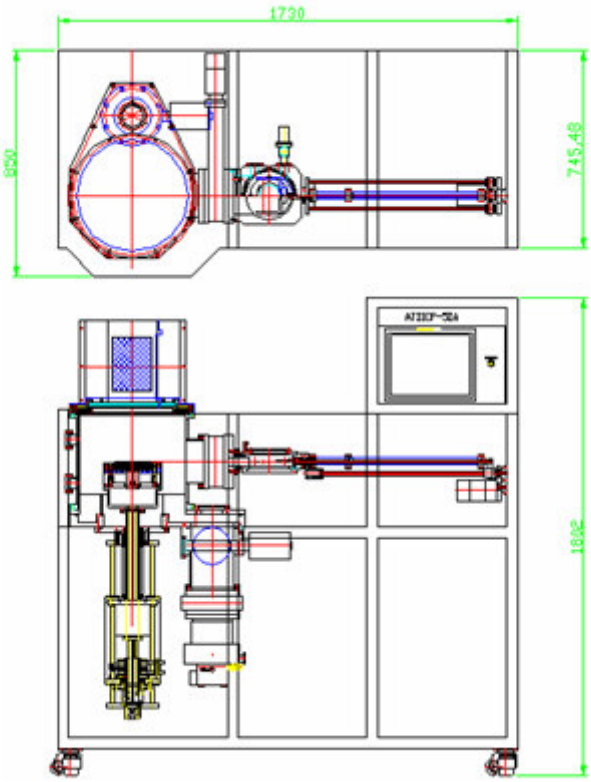
Special Features

- Small rf-PECVD system for CNT(Carbon Nano Tube) synthesis
- Low temperature synthesis of CNTs (under about 400℃)
- Heating range
  400 ~ 600℃
- Applications
  CNTs growth

- Wafer capacity
  1 × 4"
- Average throughput
  Up to 5,000 wafers per year
- Dimension
  800L × 1100H × 600W (㎜)
- Others
  Power: AC 100W (13.56MHz)
  Gas : $NH_3/C_2H_2(CH_4)/Ar$
  Heater : silicon carbide
  (heating rate: 40℃/min, max. temp.:850℃, deviation: negligible)
  Pump: rotary(600l/min) & turbo(450l/s)

SYSTEM

◇ Layout



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